

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 10-095699  
 (43)Date of publication of application : 14.04.1998

51)Int.Cl.

C30B 29/10  
 C30B 13/28  
 H01J 1/30  
 H01J 9/02

21)Application number : 08-265574

(71)Applicant : NATL INST FOR RES IN INORG  
MATER

22)Date of filing : 13.09.1996

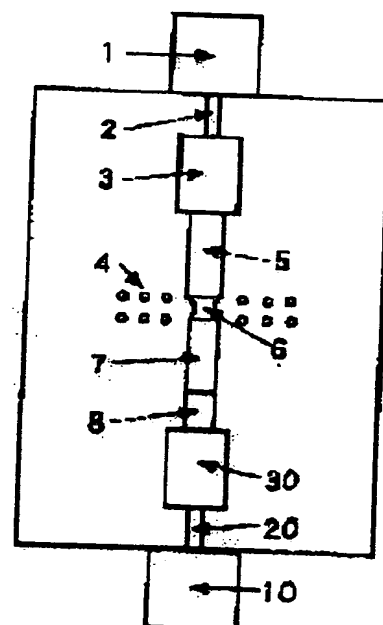
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## 54) GROWTH OF ZIRCONIUM DIBORIDE SINGLE CRYSTAL

## 57)Abstract:

**PROBLEM TO BE SOLVED:** To enable the growth of  $ZrB_2$  single crystal of good quality, free from crystal defect (sub-boundary structure), by growing the crystal in a He gas atmosphere and specifying the melting zone composition and the growing speed, when  $ZrB_2$  single crystal is grown through the floating zone technique.

**SOLUTION:** A  $ZrB_2$  powder and a B powder are mixed at a specific ratio, the powder is compressed into a bar and the bar is sintered under prescribed conditions to prepare a starting sintered bar 5. The sintered bar 5 is fixed through a holder 3 to the upper shaft 2, and through the holder 30 to a lower shaft 20 thereby fixing the sintered bar 8 for forming the initial melting zone. A sintered boron (B) is inserted between the sintered bar 8 and the starting sintered bar 5 and the sintered boron and its periphery are heated by a work coil with high-frequency current to form the melting zone 6 and the melting zone is allowed to move downward between the upper shaft 2 to the lower shaft 20 thereby growing the single crystal 7. This process is carried out in an atmosphere of He gas, preferably at about 3-15 atmospheric pressure and the molecular ratio B/Zr (atomic ratio) in the melting zone composition is set to about 1.5-2.8 and the growth speed is set to 3-10 cm/hour.



## 58)LEGAL STATUS

Date of request for examination]

13.09.1996

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[Date of sending the examiner's decision of rejection] 22.06.1999

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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